

# RF Power LDMOS Transistor

## N-Channel Enhancement-Mode Lateral MOSFET

Designed for wideband defense, industrial and commercial applications with frequencies up to 1000 MHz. The high gain and broadband performance of this device are ideal for large-signal, common-source amplifier applications in 28 V RF systems.

- Typical Single-Carrier N-CDMA Performance @ 880 MHz,  $V_{DD} = 28$  Vdc,  $I_{DQ} = 450$  mA,  $P_{out} = 14$  W Avg., IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.  
Power Gain — 21.1 dB  
Drain Efficiency — 33%  
ACPR @ 750 kHz Offset — -45.7 dBc in 30 kHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 32 Vdc, 880 MHz, 3 dB Overdrive, Designed for Enhanced Ruggedness

### GSM EDGE Application

- Typical GSM EDGE Performance:  $V_{DD} = 28$  Vdc,  $I_{DQ} = 500$  mA,  $P_{out} = 21$  W Avg., Full Frequency Band (920-960 MHz)  
Power Gain — 20 dB  
Drain Efficiency — 46%  
Spectral Regrowth @ 400 kHz Offset = -62 dBc  
Spectral Regrowth @ 600 kHz Offset = -78 dBc  
EVM — 1.5% rms

### GSM Application

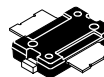
- Typical GSM Performance:  $V_{DD} = 28$  Vdc,  $I_{DQ} = 500$  mA,  $P_{out} = 60$  W, Full Frequency Band (920-960 MHz)  
Power Gain — 20 dB  
Drain Efficiency — 63%

### Features

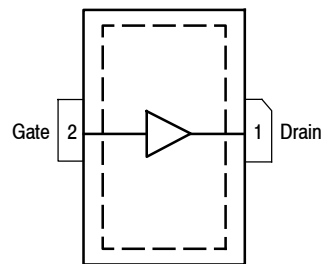
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Integrated ESD Protection
- 225°C Capable Plastic Package
- In Tape and Reel. R1 Suffix = 500 Units, 24 mm Tape Width, 13-inch Reel.

**MMRF1315NR1**

**500-1000 MHz, 60 W CW, 28 V  
BROADBAND  
RF POWER LDMOS TRANSISTOR**



**TO-270-2  
PLASTIC**



(Top View)

Note: The backside of the package is the source terminal for the transistor.

**Figure 1. Pin Connections**

**Table 1. Maximum Ratings**

| Rating                               | Symbol    | Value       | Unit |
|--------------------------------------|-----------|-------------|------|
| Drain-Source Voltage                 | $V_{DSS}$ | -0.5, +66   | Vdc  |
| Gate-Source Voltage                  | $V_{GS}$  | -0.5, +12   | Vdc  |
| Maximum Operation Voltage            | $V_{DD}$  | 32, +0      | Vdc  |
| Storage Temperature Range            | $T_{stg}$ | -65 to +150 | °C   |
| Case Operating Temperature           | $T_C$     | 150         | °C   |
| Operating Junction Temperature (1,2) | $T_J$     | 225         | °C   |

**Table 2. Thermal Characteristics**

| Characteristic                                                                                           | Symbol          | Value (2,3)  | Unit |
|----------------------------------------------------------------------------------------------------------|-----------------|--------------|------|
| Thermal Resistance, Junction to Case<br>Case Temperature 80°C, 60 W CW<br>Case Temperature 78°C, 14 W CW | $R_{\theta JC}$ | 0.77<br>0.88 | °C/W |

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools (Software & Tools)/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**Table 3. ESD Protection Characteristics**

| Test Methodology                      | Class |
|---------------------------------------|-------|
| Human Body Model (per JESD22-A114)    | 1B    |
| Machine Model (per EIA/JESD22-A115)   | A     |
| Charge Device Model (per JESD22-C101) | IV    |

**Table 4. Moisture Sensitivity Level**

| Test Methodology                      | Rating | Package Peak Temperature | Unit |
|---------------------------------------|--------|--------------------------|------|
| Per JESD 22-A113, IPC/JEDEC J-STD-020 | 3      | 260                      | °C   |

**Table 5. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

**Off Characteristics**

|                                                                                                   |           |   |   |    |                 |
|---------------------------------------------------------------------------------------------------|-----------|---|---|----|-----------------|
| Zero Gate Voltage Drain Leakage Current<br>( $V_{DS} = 66\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ ) | $I_{DSS}$ | — | — | 10 | $\mu\text{Adc}$ |
| Zero Gate Voltage Drain Leakage Current<br>( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ ) | $I_{DSS}$ | — | — | 1  | $\mu\text{Adc}$ |
| Gate-Source Leakage Current<br>( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )              | $I_{GSS}$ | — | — | 10 | $\mu\text{Adc}$ |

**On Characteristics**

|                                                                                                               |              |      |      |     |     |
|---------------------------------------------------------------------------------------------------------------|--------------|------|------|-----|-----|
| Gate Threshold Voltage<br>( $V_{DS} = 10\text{ Vdc}$ , $I_D = 200\text{ }\mu\text{A}$ )                       | $V_{GS(th)}$ | 1    | 2.2  | 3   | Vdc |
| Gate Quiescent Voltage<br>( $V_{DD} = 28\text{ Vdc}$ , $I_D = 450\text{ mAdc}$ , Measured in Functional Test) | $V_{GS(Q)}$  | 2    | 3    | 4   | Vdc |
| Drain-Source On-Voltage<br>( $V_{GS} = 10\text{ Vdc}$ , $I_D = 1.5\text{ Adc}$ )                              | $V_{DS(on)}$ | 0.05 | 0.27 | 0.4 | Vdc |

**Dynamic Characteristics**

|                                                                                                                       |           |   |     |   |    |
|-----------------------------------------------------------------------------------------------------------------------|-----------|---|-----|---|----|
| Reverse Transfer Capacitance<br>( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ ) | $C_{rss}$ | — | 1.1 | — | pF |
| Output Capacitance<br>( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )           | $C_{oss}$ | — | 33  | — | pF |
| Input Capacitance<br>( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)            | $C_{iss}$ | — | 109 | — | pF |

**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 450\text{ mA}$ ,  $P_{out} = 14\text{ W Avg.}$ ,  $f = 880\text{ MHz}$ , Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Channel Bandwidth @  $\pm 750\text{ kHz}$  Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF

|                              |          |      |       |     |     |
|------------------------------|----------|------|-------|-----|-----|
| Power Gain                   | $G_{ps}$ | 20   | 21.1  | 23  | dB  |
| Drain Efficiency             | $\eta_D$ | 30.5 | 33    | —   | %   |
| Adjacent Channel Power Ratio | ACPR     | —    | -45.7 | -44 | dBc |
| Input Return Loss            | IRL      | —    | -18   | -9  | dB  |

(continued)

**Table 5. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted) (continued)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

**Typical GSM EDGE Performances** (In Freescale GSM EDGE Test Fixture Optimized for 920–960 MHz, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 500\text{ mA}$ ,  $P_{out} = 21\text{ W Avg.}$ ,  $f = 920\text{--}960\text{ MHz}$ , GSM EDGE Signal

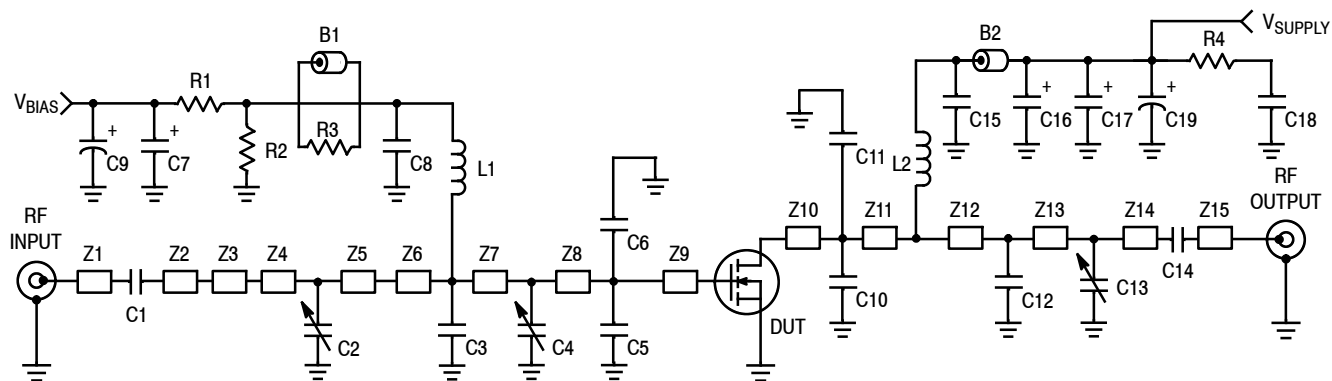
|                                     |          |   |     |   |     |
|-------------------------------------|----------|---|-----|---|-----|
| Power Gain                          | $G_{ps}$ | — | 20  | — | dB  |
| Drain Efficiency                    | $\eta_D$ | — | 46  | — | %   |
| Error Vector Magnitude              | EVM      | — | 1.5 | — | %   |
| Spectral Regrowth at 400 kHz Offset | SR1      | — | -62 | — | dBc |
| Spectral Regrowth at 600 kHz Offset | SR2      | — | -78 | — | dBc |

**Typical CW Performances** (In Freescale GSM Test Fixture Optimized for 920–960 MHz, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 500\text{ mA}$ ,  $P_{out} = 60\text{ W}$ ,  $f = 920\text{--}960\text{ MHz}$

|                                                                |          |   |     |   |    |
|----------------------------------------------------------------|----------|---|-----|---|----|
| Power Gain                                                     | $G_{ps}$ | — | 20  | — | dB |
| Drain Efficiency                                               | $\eta_D$ | — | 63  | — | %  |
| Input Return Loss                                              | IRL      | — | -12 | — | dB |
| $P_{out}$ @ 1 dB Compression Point<br>( $f = 940\text{ MHz}$ ) | P1dB     | — | 67  | — | W  |

**Typical Performances** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 450\text{ mA}$ , 865–900 MHz Bandwidth

|                                                                                                                                                                                             |               |   |       |   |                       |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|---|-------|---|-----------------------|
| Video Bandwidth @ 60 W PEP $P_{out}$ where $IM3 = -30\text{ dBc}$<br>(Tone Spacing from 100 kHz to VBW)<br>$\Delta IMD3 = IMD3$ @ VBW frequency - $IMD3$ @ 100 kHz < 1 dBc (both sidebands) | VBW           | — | 3     | — | MHz                   |
| Gain Flatness in 35 MHz Bandwidth @ $P_{out} = 14\text{ W Avg.}$                                                                                                                            | $G_F$         | — | 0.27  | — | dB                    |
| Gain Variation over Temperature<br>( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ )                                                                                                           | $\Delta G$    | — | 0.011 | — | dB/ $^\circ\text{C}$  |
| Output Power Variation over Temperature<br>( $-30^\circ\text{C}$ to $+85^\circ\text{C}$ )                                                                                                   | $\Delta P1dB$ | — | 0.088 | — | dBm/ $^\circ\text{C}$ |



|    |                                |     |                                          |
|----|--------------------------------|-----|------------------------------------------|
| Z1 | 0.215" x 0.065" Microstrip     | Z9  | 0.057" x 0.525" Microstrip               |
| Z2 | 0.221" x 0.065" Microstrip     | Z10 | 0.360" x 0.270" Microstrip               |
| Z3 | 0.500" x 0.100" Microstrip     | Z11 | 0.063" x 0.270" Microstrip               |
| Z4 | 0.460" x 0.270" Microstrip     | Z12 | 0.360" x 0.065" Microstrip               |
| Z5 | 0.040" x 0.270" Microstrip     | Z13 | 0.170" x 0.065" Microstrip               |
| Z6 | 0.280" x 0.270" x 0.530" Taper | Z14 | 0.880" x 0.065" Microstrip               |
| Z7 | 0.087" x 0.525" Microstrip     | Z15 | 0.260" x 0.065" Microstrip               |
| Z8 | 0.435" x 0.525" Microstrip     | PCB | Taconic RF-35 0.030", $\epsilon_r = 3.5$ |

**Figure 2. MMRF1315NR1 Test Circuit Schematic**

**Table 6. MMRF1315NR1 Test Circuit Component Designations and Values**

| Part             | Description                              | Part Number         | Manufacturer |
|------------------|------------------------------------------|---------------------|--------------|
| B1               | Ferrite Bead                             | 2743019447          | Fair Rite    |
| B2               | Ferrite Bead                             | 274021447           | Fair Rite    |
| C1, C8, C14, C15 | 47 pF Chip Capacitors                    | ATC100B470JT500XT   | ATC          |
| C2, C4, C13      | 0.8–8.0 pF Variable Capacitors, Gigatrim | 2729152             | Johanson     |
| C3               | 3.0 pF Chip Capacitor                    | ATC100B3R0JT500XT   | ATC          |
| C5, C6           | 15 pF Chip Capacitors                    | ATC100B150JT500XT   | ATC          |
| C7, C16, C17     | 10 $\mu$ F, 35 V Tantalum Capacitors     | T491D106K035AT      | Kemet        |
| C9               | 100 $\mu$ F, 50 V Electrolytic Capacitor | MCHT101M1HB-1017-RH | Multicomp    |
| C10, C11         | 12 pF Chip Capacitors                    | ATC100B120JT500XT   | ATC          |
| C12              | 4.3 pF Chip Capacitor                    | ATC100B4R3JT500XT   | ATC          |
| C18              | 0.56 $\mu$ F Chip Capacitor              | ATC700A561MT150XT   | ATC          |
| C19              | 470 $\mu$ F, 63 V Electrolytic Capacitor | EKME630ELL471MK255  | Multicomp    |
| L1, L2           | 12.5 nH Inductor                         | A04T-5              | Coilcraft    |
| R1               | 1 k $\Omega$ , 1/4 W Chip Resistor       | CRCW12061001FKEA    | Vishay       |
| R2               | 560 k $\Omega$ , 1/4 W Chip Resistor     | CRCW12065600FKEA    | Vishay       |
| R3               | 12 $\Omega$ , 1/4 W Chip Resistor        | CRCW120612R0FKEA    | Vishay       |
| R4               | 27 $\Omega$ , 1/4 W Chip Resistor        | CRCW120627R0FKEA    | Vishay       |

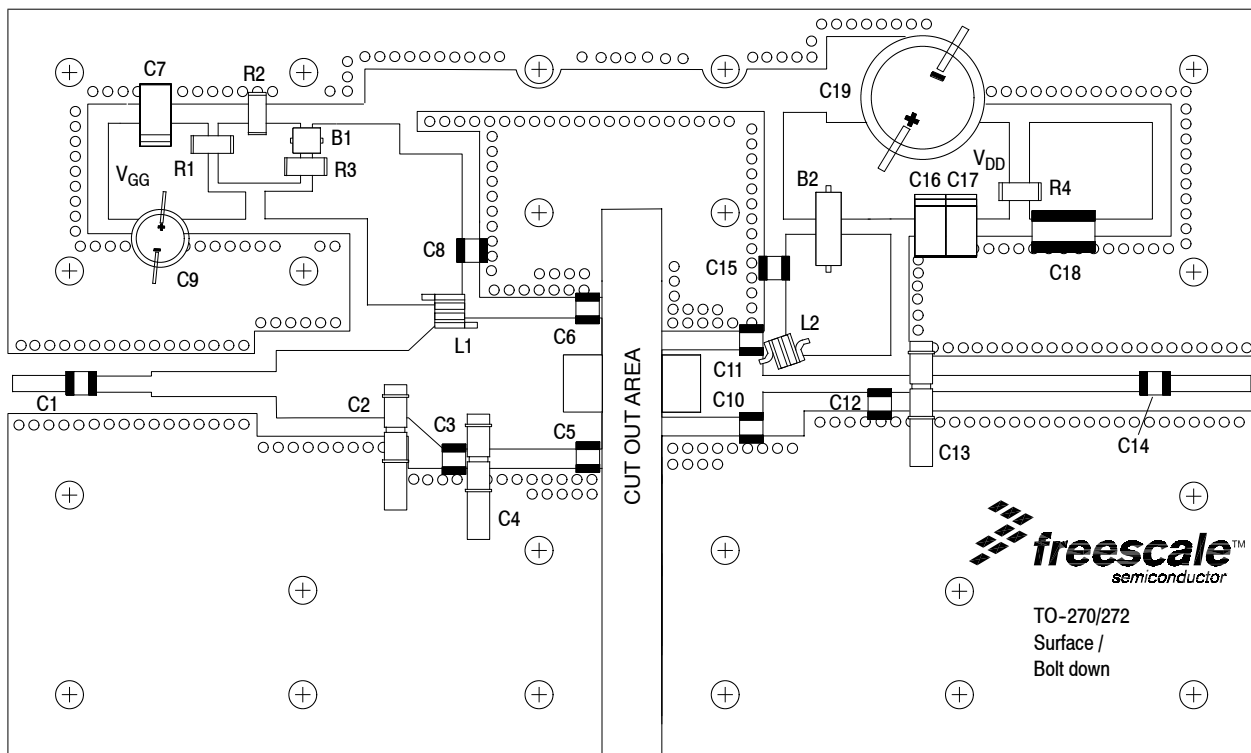
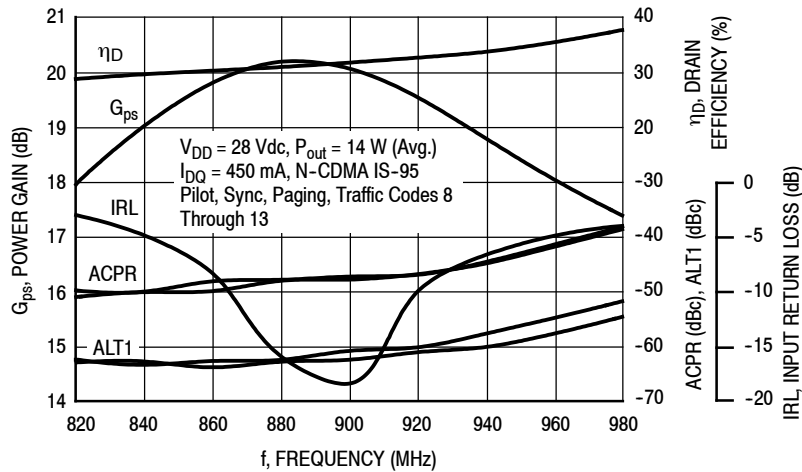
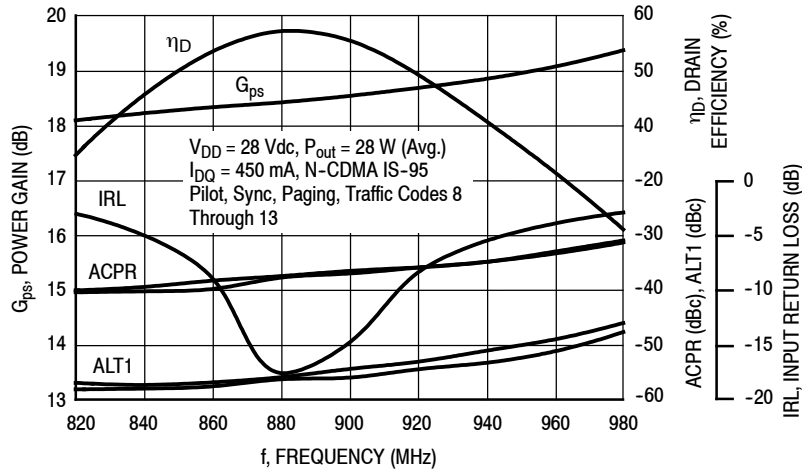


Figure 3. MMRF1315NR1 Test Circuit Component Layout

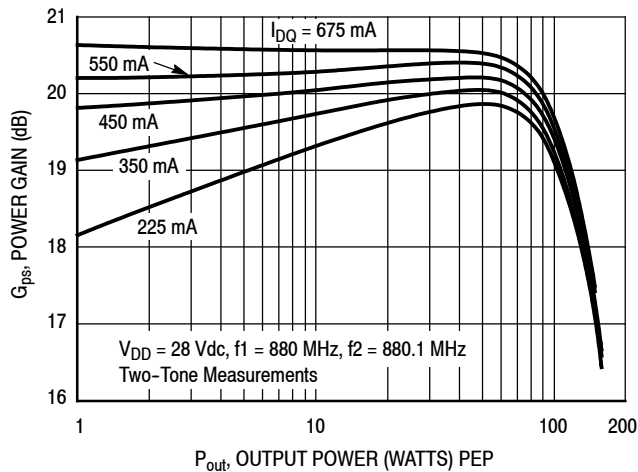
## TYPICAL CHARACTERISTICS



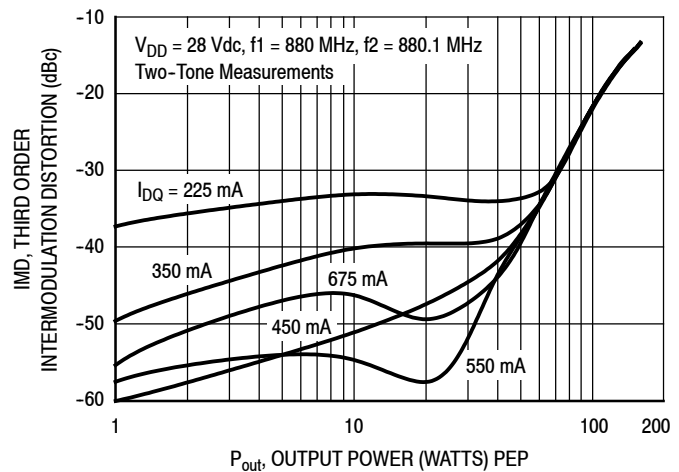
**Figure 4. Single-Carrier N-CDMA Broadband Performance  
@  $P_{out} = 14$  Watts Avg.**



**Figure 5. Single-Carrier N-CDMA Broadband Performance  
@  $P_{out} = 28$  Watts Avg.**

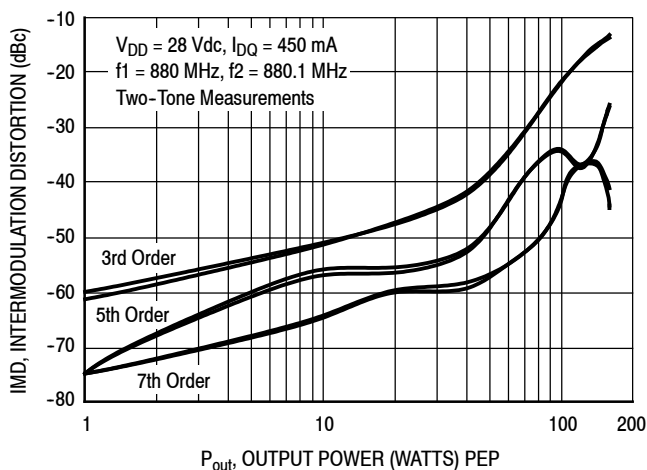


**Figure 6. Two-Tone Power Gain versus  
Output Power**

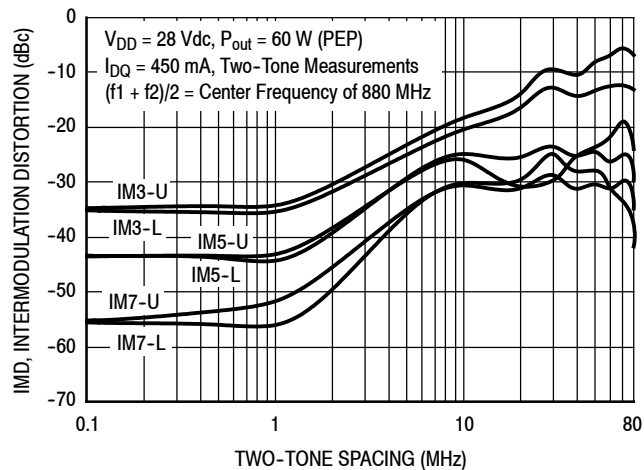


**Figure 7. Third Order Intermodulation Distortion  
versus Output Power**

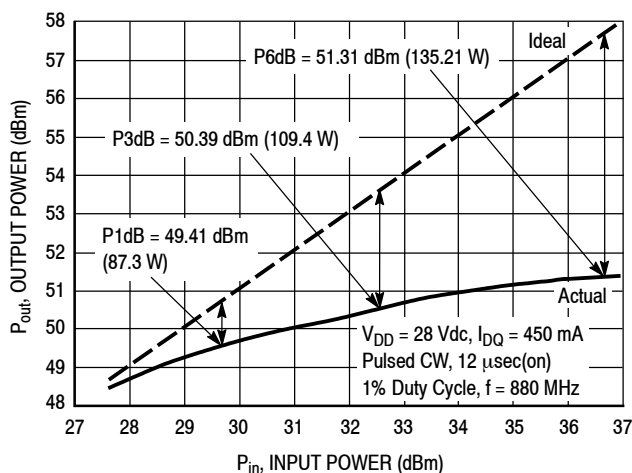
## TYPICAL CHARACTERISTICS



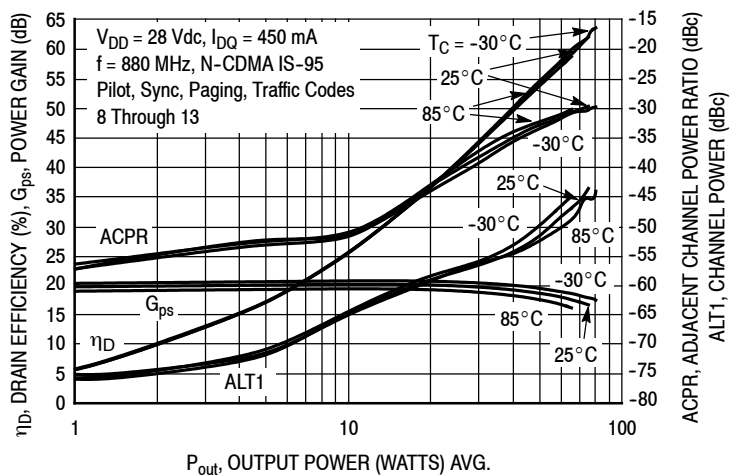
**Figure 8. Intermodulation Distortion Products versus Output Power**



**Figure 9. Intermodulation Distortion Products versus Tone Spacing**

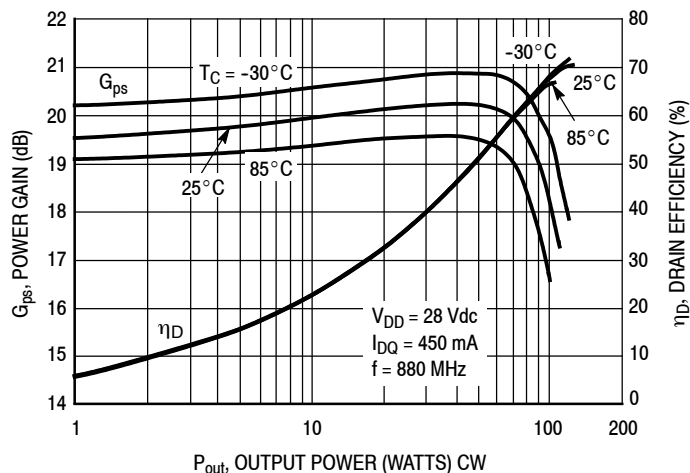


**Figure 10. Pulsed CW Output Power versus Input Power**

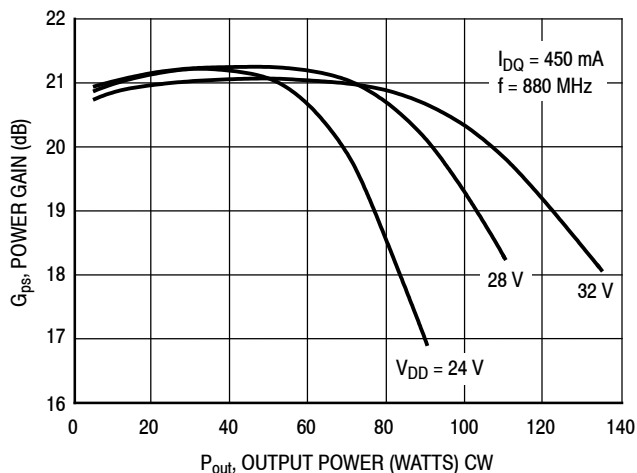


**Figure 11. Single-Carrier N-CDMA ACPR, ALT1, Power Gain and Drain Efficiency versus Output Power**

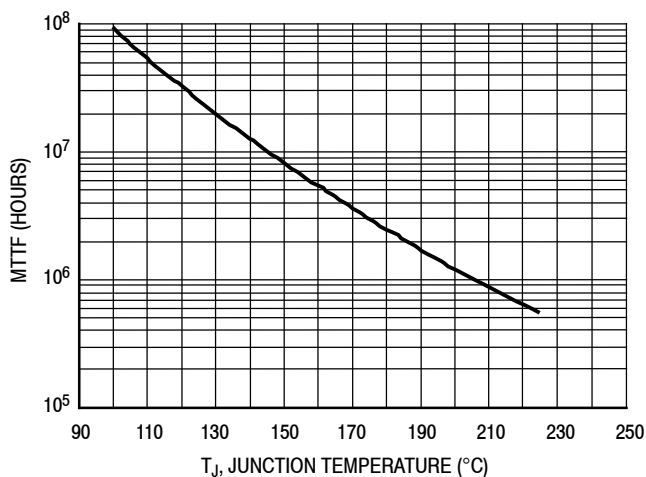
## TYPICAL CHARACTERISTICS



**Figure 12. Power Gain and Drain Efficiency versus CW Output Power**



**Figure 13. Power Gain versus Output Power**



This above graph displays calculated MTTF in hours when the device is operated at  $V_{DD} = 28$  Vdc,  $P_{out} = 14$  W Avg., and  $\eta_D = 32.5\%$ .

MTTF calculator available at <http://www.freescale.com/rf.SelectTools> (Software & Tools)/Calculators to access MTTF calculators by product.

**Figure 14. MTTF versus Junction Temperature**

# N-CDMA TEST SIGNAL

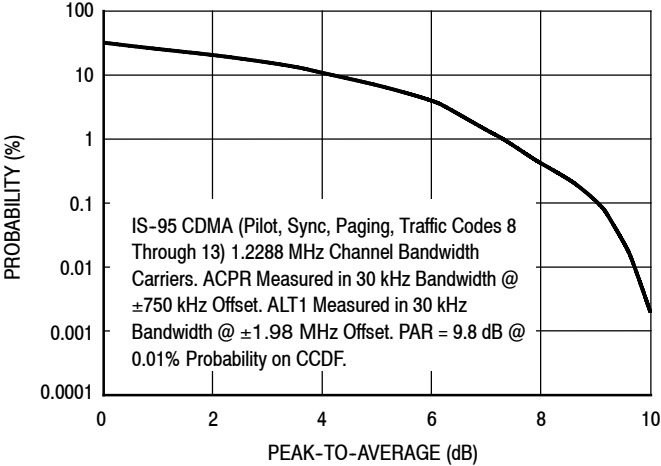


Figure 15. Single-Carrier CCDF N-CDMA

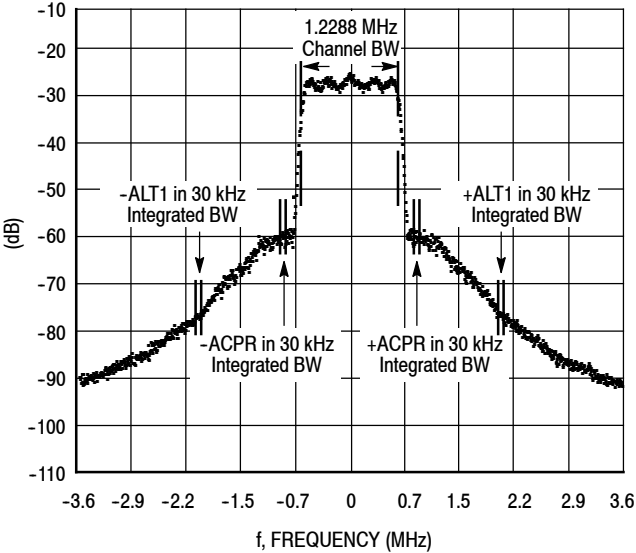
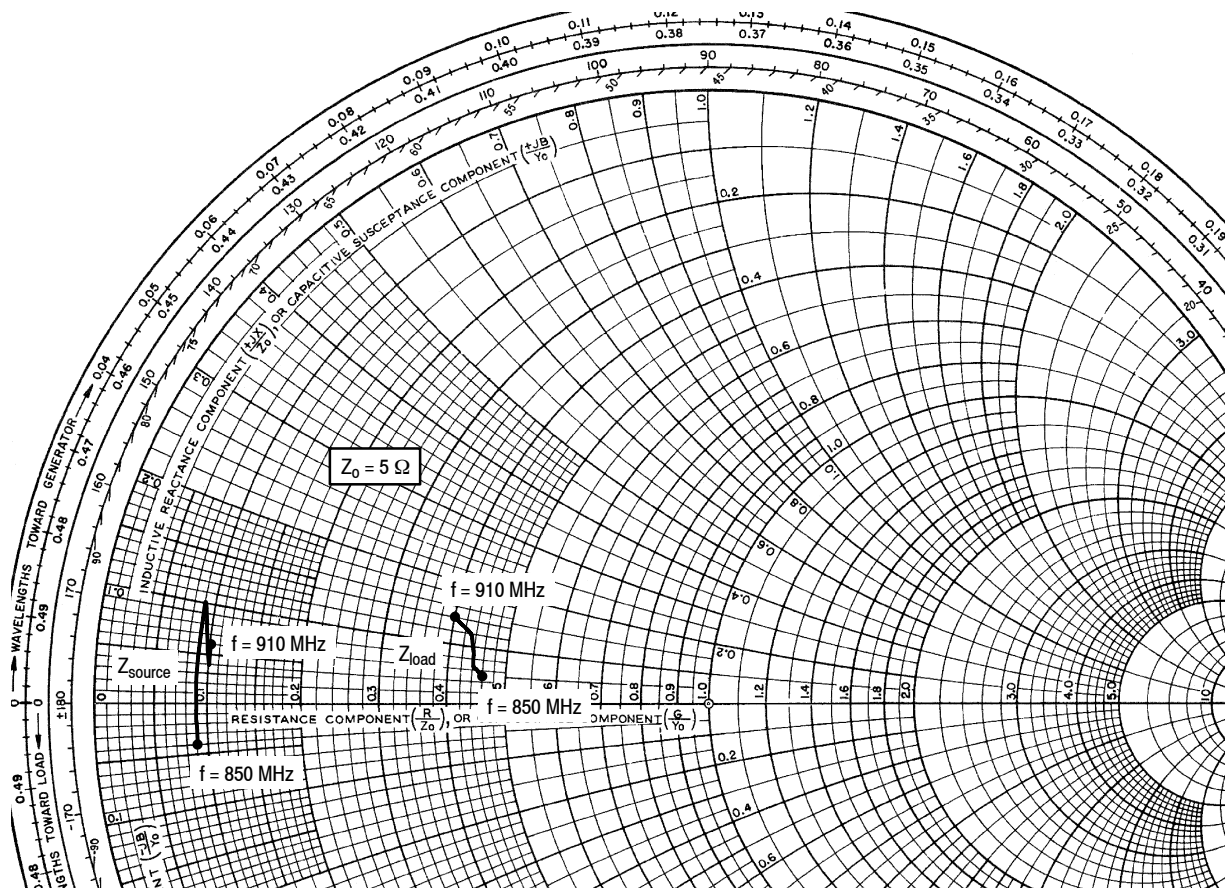


Figure 16. Single-Carrier N-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 450 \text{ mA}$ ,  $P_{out} = 14 \text{ W Avg.}$

| f<br>MHz | $Z_{source}$<br>$\Omega$ | $Z_{load}$<br>$\Omega$ |
|----------|--------------------------|------------------------|
| 850      | $0.44 - j0.20$           | $2.28 + j0.23$         |
| 865      | $0.44 - j0.07$           | $2.18 + j0.33$         |
| 880      | $0.45 + j0.50$           | $2.20 + j0.47$         |
| 895      | $0.48 + j0.18$           | $2.15 + j0.61$         |
| 910      | $0.52 + j0.29$           | $2.00 + j0.68$         |

$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

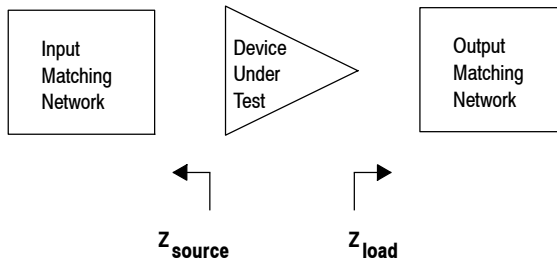
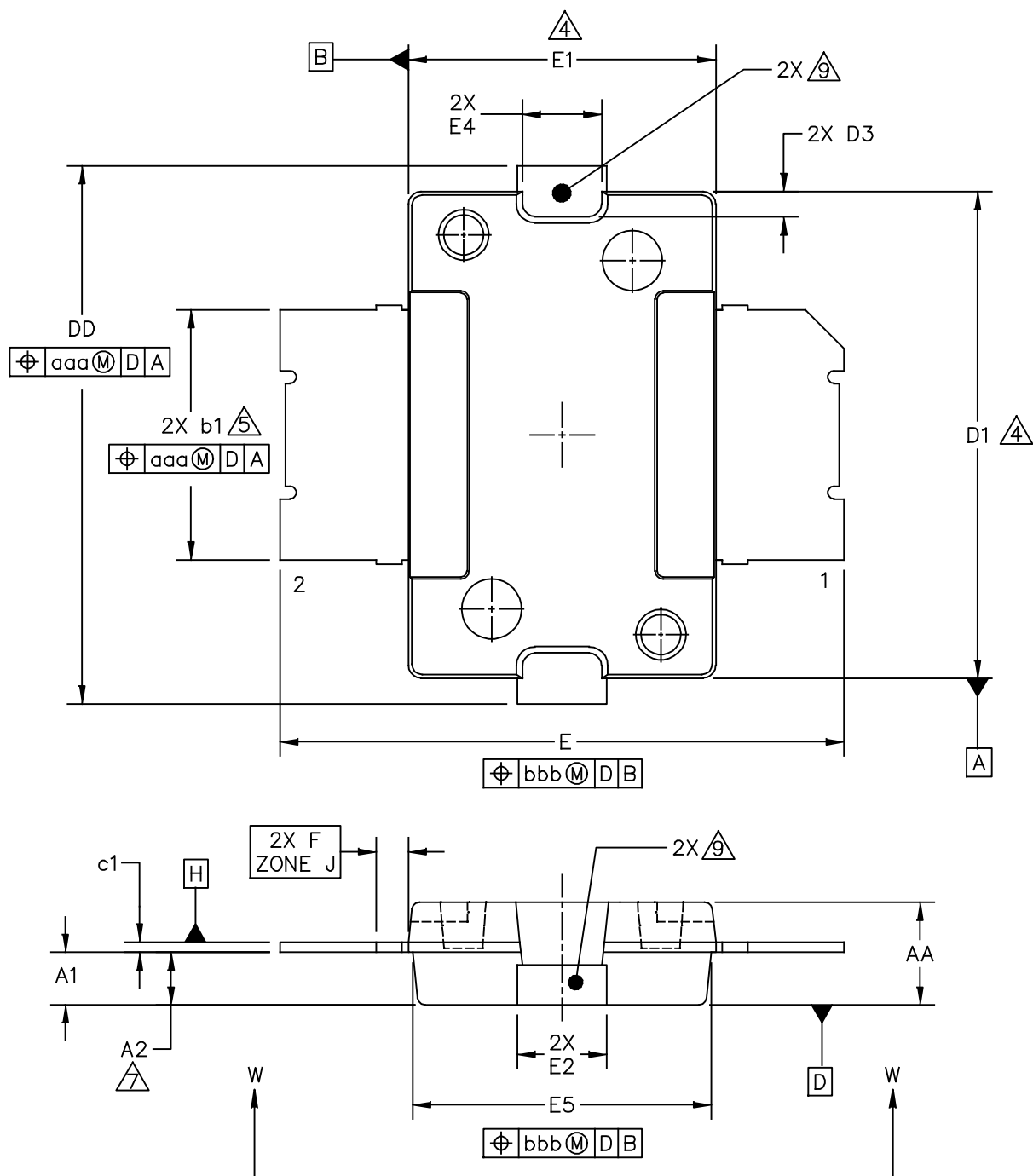
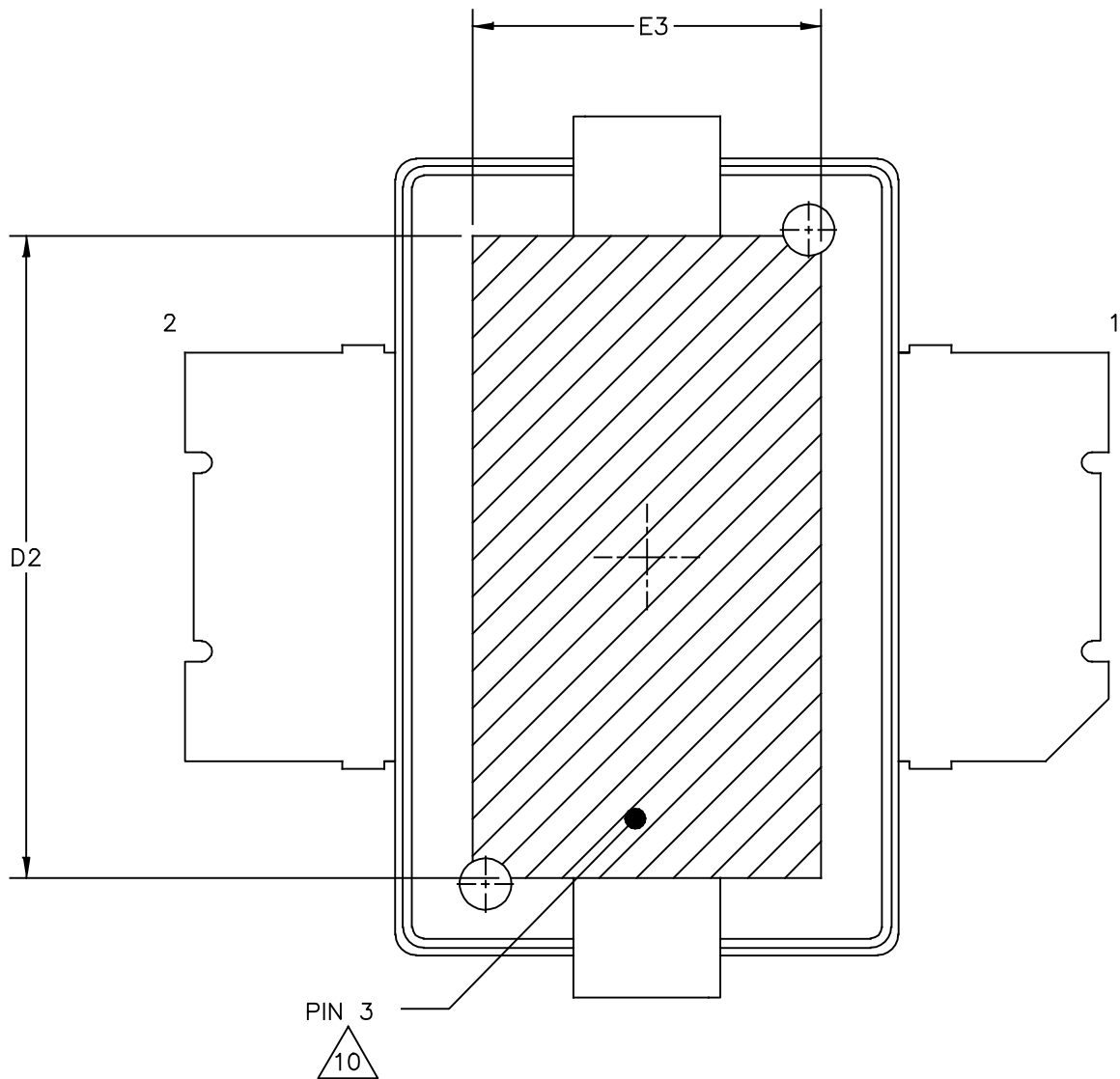


Figure 17. Series Equivalent Source and Load Impedance

## PACKAGE DIMENSIONS



|                                                         |  |                    |                          |                            |        |
|---------------------------------------------------------|--|--------------------|--------------------------|----------------------------|--------|
| © FREESCALE SEMICONDUCTOR, INC.<br>ALL RIGHTS RESERVED. |  | MECHANICAL OUTLINE |                          | PRINT VERSION NOT TO SCALE |        |
| TITLE:<br><br>TO-270-2                                  |  |                    | DOCUMENT NO: 98ASH98117A |                            | REV: P |
|                                                         |  |                    | STANDARD: NON-JEDEC      |                            |        |
|                                                         |  |                    | 02 JUN 2014              |                            |        |



VIEW W-W  
BOTTOM VIEW

|                                                         |                                      |                            |
|---------------------------------------------------------|--------------------------------------|----------------------------|
| © FREESCALE SEMICONDUCTOR, INC.<br>ALL RIGHTS RESERVED. | MECHANICAL OUTLINE                   | PRINT VERSION NOT TO SCALE |
| TITLE:<br><br>TO-270-2                                  | DOCUMENT NO: 98ASH98117A      REV: P |                            |
|                                                         | STANDARD: NON-JEDEC                  |                            |
|                                                         | 02 JUN 2014                          |                            |

# NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE H IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 INCH (0.15 MM) PER SIDE. DIMENSIONS D1 AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
5. DIMENSION b1 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 INCH (0.13 MM) TOTAL IN EXCESS OF THE b1 DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS A AND B TO BE DETERMINED AT DATUM PLANE H.
7. DIMENSION A2 APPLIES WITHIN ZONE J ONLY.
8. DIMENSIONS DD AND E2 DO NOT INCLUDE MOLD PROTRUSION. OVERALL LENGTH INCLUDING MOLD PROTRUSION SHOULD NOT EXCEED 0.430 INCH (10.92 MM) FOR DIMENSION DD AND 0.080 INCH (2.03 MM) FOR DIMENSION E2. DIMENSIONS DD AND E2 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE D.
9. THESE SURFACES OF THE HEAT SLUG ARE NOT PART OF THE SOLDERABLE SURFACES AND MAY REMAIN UNPLATED.
10. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG. DIMENSIONS D2 AND E3 REPRESENT THE VALUES BETWEEN THE TWO OPPOSITE POINTS ALONG THE EDGES OF EXPOSED AREA OF THE HEAT SLUG.

| INCH                                                    |      |       | MILLIMETER         |       | INCH                                                 |                            |      | MILLIMETER |      |
|---------------------------------------------------------|------|-------|--------------------|-------|------------------------------------------------------|----------------------------|------|------------|------|
| DIM                                                     | MIN  | MAX   | MIN                | MAX   | DIM                                                  | MIN                        | MAX  | MIN        | MAX  |
| AA                                                      | .078 | .082  | 1.98               | 2.08  | E4                                                   | .058                       | .066 | 1.47       | 1.68 |
| A1                                                      | .039 | .043  | 0.99               | 1.09  | E5                                                   | .231                       | .235 | 5.87       | 5.97 |
| A2                                                      | .040 | .042  | 1.02               | 1.07  | F                                                    | .025 BSC                   |      | 0.64 BSC   |      |
| DD                                                      | .416 | .424  | 10.57              | 10.77 | b1                                                   | .193                       | .199 | 4.90       | 5.06 |
| D1                                                      | .378 | .382  | 9.60               | 9.70  | c1                                                   | .007                       | .011 | 0.18       | 0.28 |
| D2                                                      | .290 | ----- | 7.37               | ----- | aaa                                                  | .004                       |      | 0.10       |      |
| D3                                                      | .016 | .024  | 0.41               | 0.61  | bbb                                                  | .008                       |      | 0.20       |      |
| E                                                       | .436 | .444  | 11.07              | 11.28 |                                                      |                            |      |            |      |
| E1                                                      | .238 | .242  | 6.04               | 6.15  |                                                      |                            |      |            |      |
| E2                                                      | .066 | .074  | 1.68               | 1.88  |                                                      |                            |      |            |      |
| E3                                                      | .150 | ----- | 3.81               | ----- |                                                      |                            |      |            |      |
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| TITLE:<br><br>TO-270-2                                  |      |       |                    |       | DOCUMENT NO: 98ASH98117A                      REV: P |                            |      |            |      |
|                                                         |      |       |                    |       | STANDARD: NON-JEDEC                                  |                            |      |            |      |
|                                                         |      |       |                    |       | 02 JUN 2014                                          |                            |      |            |      |

## PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following resources to aid your design process.

### Application Notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Over-Molded Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

### Software

- Electromigration MTTF Calculator

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

## REVISION HISTORY

The following table summarizes revisions to this document.

| Revision | Date      | Description                                                                       |
|----------|-----------|-----------------------------------------------------------------------------------|
| 0        | July 2014 | <ul style="list-style-type: none"> <li>• Initial Release of Data Sheet</li> </ul> |

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